		17 H 402000	
BRS	904	image near2 sens\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	51	(image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
BRS	2768	(deep near2 well).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
BRS (8	(image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well).ab.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
BRS 1	150454	inplant or implant or inplanting or implanting	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
BRS 8		(second! or another or additional\$4 or deep\$4) near4 (inplant or implant or inplanting) near4 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
		51 276 3 3 150,	51 2768 ((3 150454 ii

	Type	7:17	1	
	1 ype		Search lext	DBs
4	BRS	22	(image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and ((second! or another or additional\$4 or deep\$4) near4 (inplant or implant or inplanting or implanting) near4 well)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	4	((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and ((second! or another or additional\$4 or deep\$4) near4 (inplant or implant or inplanting or implanting) near4 well)) not (((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	-	lixin-zhao.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	2	6586789.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	Ĭ		("5416345" "5898195" "5904493" "6051447").PN.	USPAT
19	BRS	0	6586789.URPN.	USPAT

	Type	e Hits	Search Text	DDC
20	BRS	5260	well near4 (micron or mu)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
21	BRS	16	(image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (well near4 (micron or mu))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
22	BRS	2	20020036303.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
23	BRS	_	20020036303.pn. and bias\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
24	BRS	41462	n near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
25	BRS	7071	p near2 (epi or epitax\$8)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
26	BRS	33799	n near2 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

B8761 photodiode or photo adj diode JPO; DE IBM_TDE IB		Typ	Hits	S arch T xt	
BRS 90479 image near2 sens\$4 mosfet or (metal adj oxide adj semiconducor misfet (n near2 substrate) and (p near2 (epi or epitax\$8)) and (n near2 well) and (photodiode or photo adj diode) and (image near2 sens\$41) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or mos or misfet) ((n near2 substrate) and (p near2 (epi or epitax\$8)) and (n near2 well) and (photodiode or photo adj diode) and (image near2 sens\$41) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or mos or mmos or misfet)) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or mos or mnos or misfet)) and (@ad < "20031710") BRS 90479 (image near2 sens\$4)	27	BRS	887	photodiode or photo adj diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
mosfet or (metal adj oxide adj semiconducor misfet (n near2 substrate) and (p near2 (epi or epitax\$8)) and (n near2 well) and (photodiode to photo adj diode) and (image near2 sens\$4 (or mos or nmos or misfet)) or pmos or epitax\$8)) and (n near2 well) and (photodiode or photo adj diode) and (image near2 sens\$4 (or mos or nmos or misfet)) or pmos or nmos or misfet)) and (@ad < "20031710") BRS 90479 (image near2 sens\$4)	78	BRS	90479	image near2 sens\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
BRS 38 BRS 38	29	BRS	186229	***********************************	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
BRS 38 BRS 90479	30	BRS	38	(n near2 substrate) and (p near2 (epi or epitax\$8)) and (n near2 well) and (photodiode or photo adj diode) and (image near2 sens\$4 and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or misfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
BRS 90479 (image near2 sens\$4)	31	BRS		((n near2 substrate) and (p near2 (epi or epitax\$8)) and (n near2 well) and (photodiode or photo adj diode) and (image near2 sens\$4 or photo adj diode) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet)) and (@ad <	USPAT; US-PGPUB; EPO; JPO; DERWENT; BM_TDB
	32	BRS	<u>ق</u>		JSPAT; JS-PGPUB; EPO; JPO; DERWENT; BM_TDB

05/12/2004, EAST Version: 1.4.1

	Typ	Hits	S arch T xt	DBs
33	BRS	2903	1 0)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
34	BRS	ಣ	(n near2 substrate) same (p near2 (epi or epitax\$8)) same (n near2 well) same (photodiode or photo adj diode) and (@ad < "20031710")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
35	BRS	88761	photodiode or photo adj diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
36	BRS	11752	deep near2 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
37	BRS	13	((((image near2 sens\$4)) near2 cmos) same (photodiode or photo adj diode)) and (deep near2 well)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
38	BRS	569	(((image near2 sens\$4)) near2 cmos) same (photodiode or photo adj diode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
39	BRS	51	((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
	BRS	467622	622 cmp or planar\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
. [BRS	15	(((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710")) and (cmp or planar\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	BRS	51	((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	BRS	15	(cmp or planar\$4) and (((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	BRS	2593	(image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (@ad < "20031710")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	BRS	56110	cmp or planariz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

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Version:
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	Typ	Hits	S arch T xt	DBs
46	BRS	160	nosfet or (metal dj (fet or field)) nisfet) and e) and (@ad < nnariz\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
47	BRS	148	(((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (@ad < "20031710") and (cmp or planariz\$4) not ((cmp or planar\$4) and ((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
48	IS&R	1557	((438/73) or (438/75) or (438/76) or (438/200)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

İ	TVD	Hite	Coscob T	
	37.		Search I XI	DBS
	BRS	90479	image near2 sens\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	BRS	186229	mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	BRS	88761	photodiode or photo adj diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	BRS	11752	deep near2 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
*	BRS	51	(image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	BRS	51	((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	BRS	88761	photodiode or photo adj diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

2